

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C
40V	1.0mΩ @ V _{GS} = 10V	225A

Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(ON)} – Minimizes On State Losses
- <1.1mm Package Profile – Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- The DMTH4001SPSQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

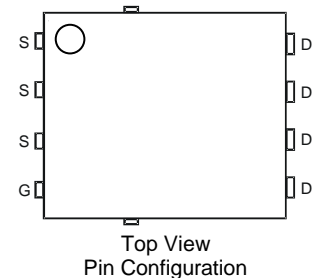
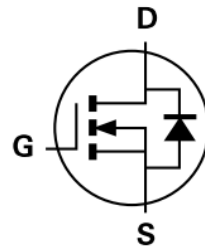
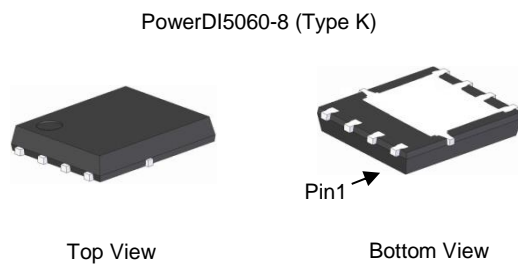
Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

Mechanical Data

- Case: PowerDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)

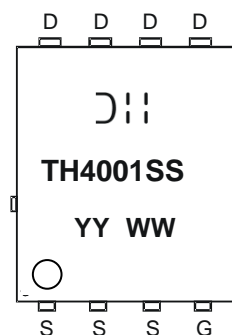


Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH4001SPSQ-13	PowerDI5060-8 (Type K)	2,500 / Tape & Reel

- Notes:
- EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



TH4001SS = Manufacturer's Marking
TH4001SS = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 21 = 2021)
WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	40	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 6)	I _D	225 160	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I _{DM}	900	A
Continuous Body Diode Forward Current (Note 6)	I _S	200	A
Pulsed Body Diode Forward Current (10μs Pulse, Duty Cycle = 1%)	I _{SM}	900	A
Avalanche Current, L = 0.1mH	I _{AS}	93.8	A
Avalanche Energy, L = 0.1mH	E _{AS}	440	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	3.1	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	48	°C/W
Total Power Dissipation (Note 6)	P _D	187.5	W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	0.8	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	40	—	—	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 32V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	2	2.61	4	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	0.73	1.0	mΩ	V _{GS} = 10V, I _D = 30A
Diode Forward Voltage	V _{SD}	—	0.7	1.3	V	V _{GS} = 0V, I _S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	10787	—	pF	V _{DS} = 20V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	—	3929	—		
Reverse Transfer Capacitance	C _{rss}	—	156	—		
Gate Resistance	R _g	—	3.71	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	—	144	—	nC	V _{DD} = 20V, I _D = 50A, V _{GS} = 10V
Gate-Source Charge	Q _{gs}	—	40	—		
Gate-Drain Charge	Q _{gd}	—	24	—		
Turn-On Delay Time	t _{D(ON)}	—	11	—	ns	V _{DD} = 20V, V _{GS} = 10V, I _D = 50A, R _g = 2.5Ω
Turn-On Rise Time	t _r	—	44	—		
Turn-Off Delay Time	t _{D(OFF)}	—	85	—		
Turn-Off Fall Time	t _f	—	38	—	ns	I _f = 15A, di/dt = 100A/μs
Reverse Recovery Time	t _{RR}	—	68	—		
Reverse Recovery Charge	Q _{RR}	—	110	—	nC	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
6. Thermal resistance from junction to soldering point (on the exposed drain pad).
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

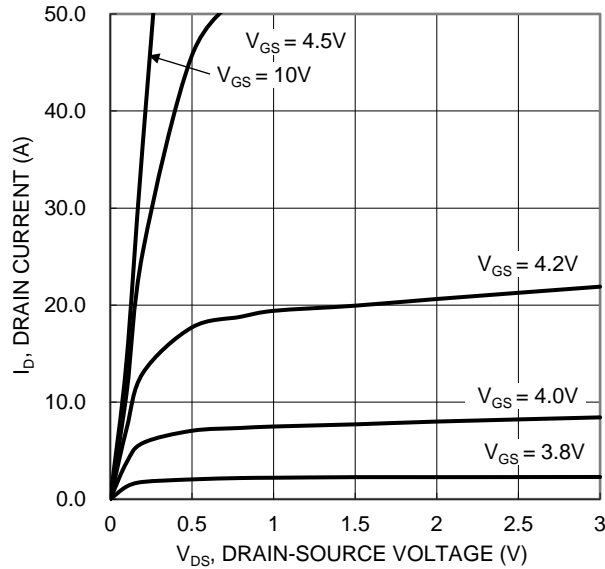


Figure 1. Typical Output Characteristic

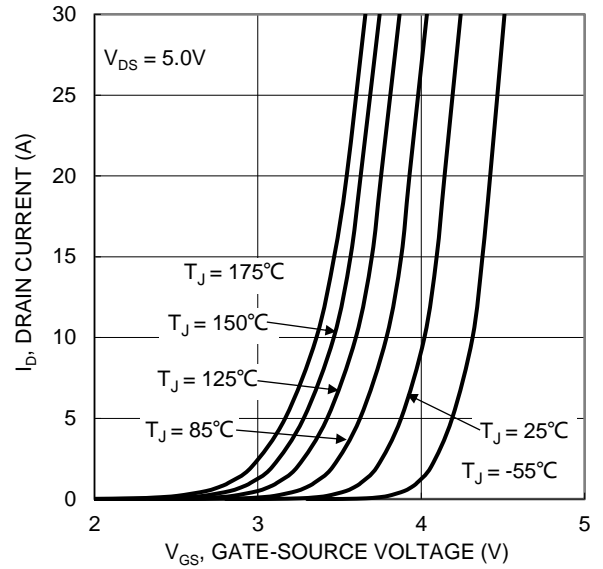


Figure 2. Typical Transfer Characteristic

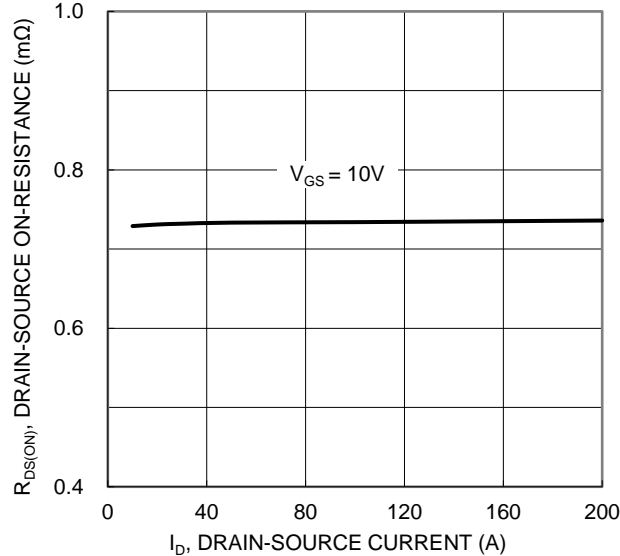


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

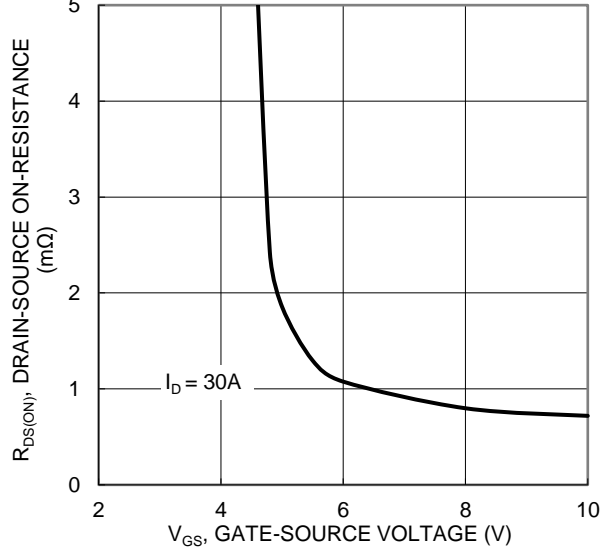


Figure 4. Typical Transfer Characteristic

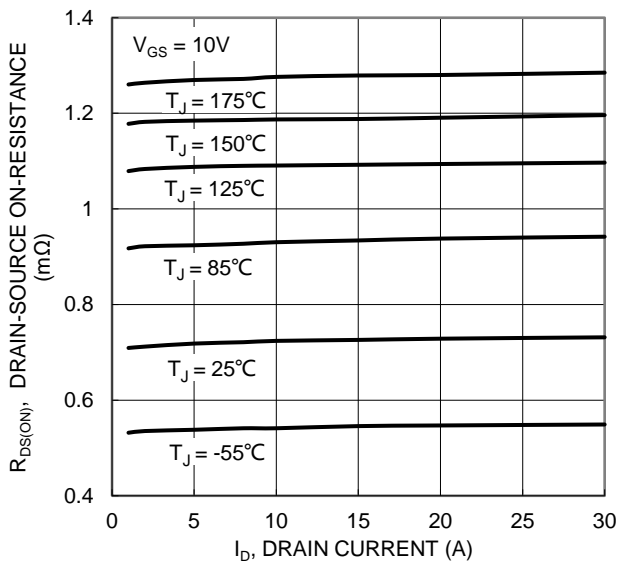


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

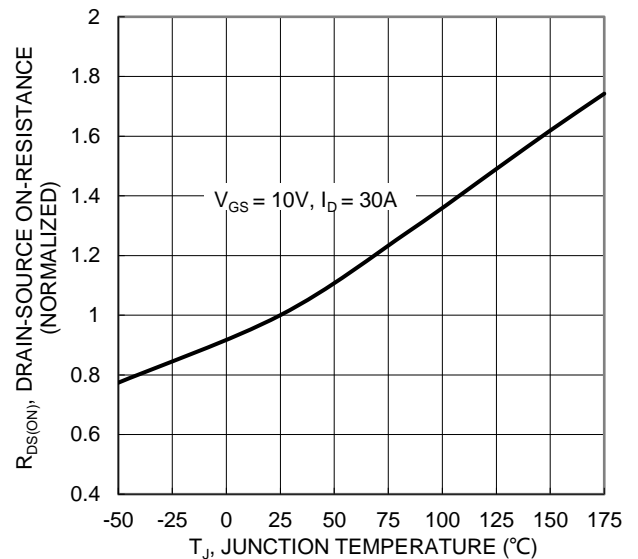


Figure 6. On-Resistance Variation with Temperature

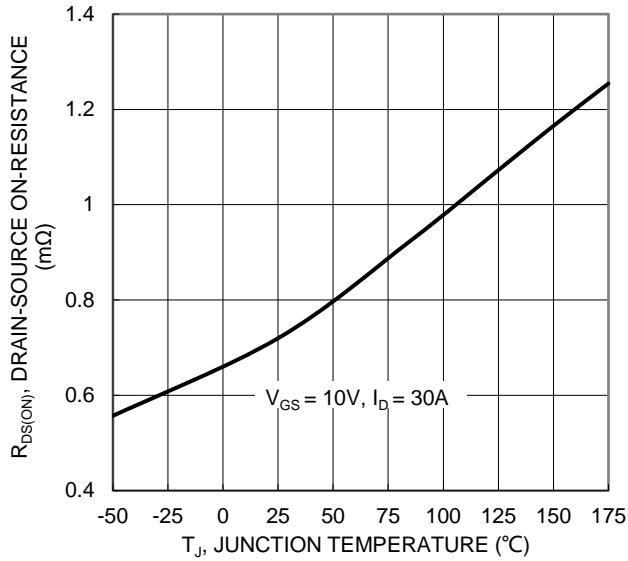


Figure 7. On-Resistance Variation with Temperature

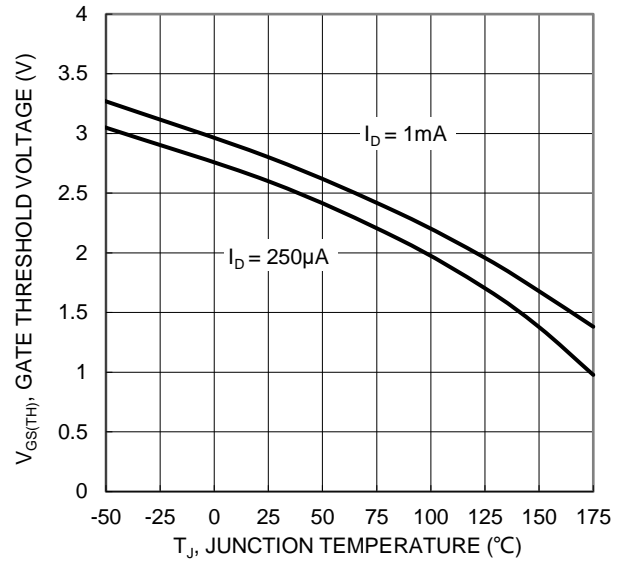


Figure 8. Gate Threshold Variation vs. Junction Temperature

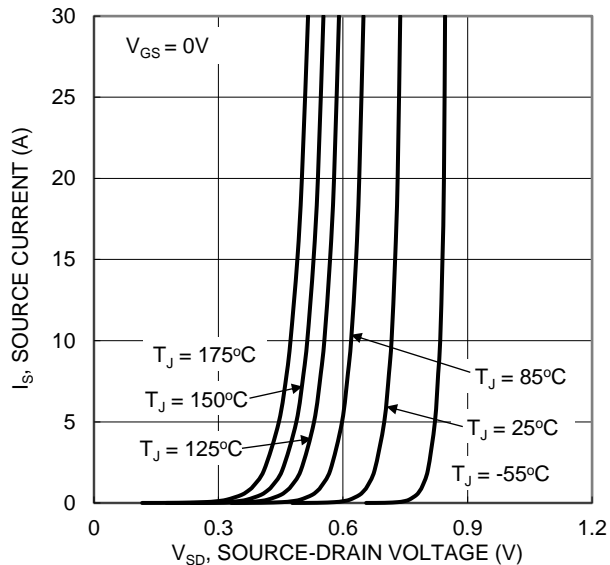


Figure 9. Diode Forward Voltage vs. Current

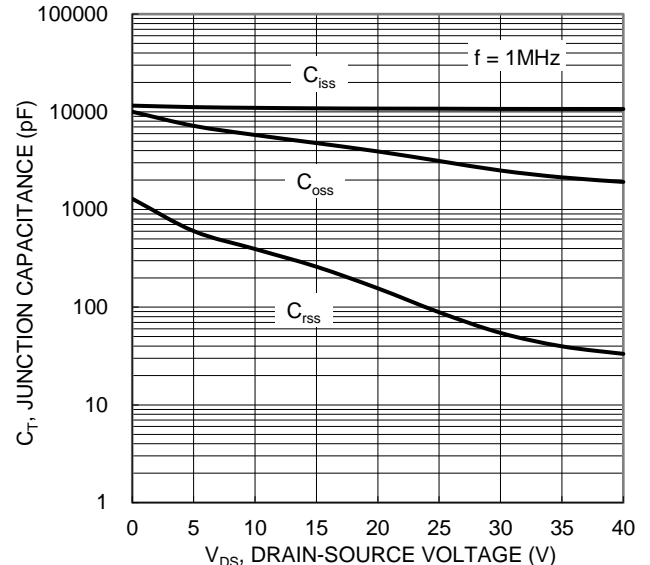


Figure 10. Typical Junction Capacitance

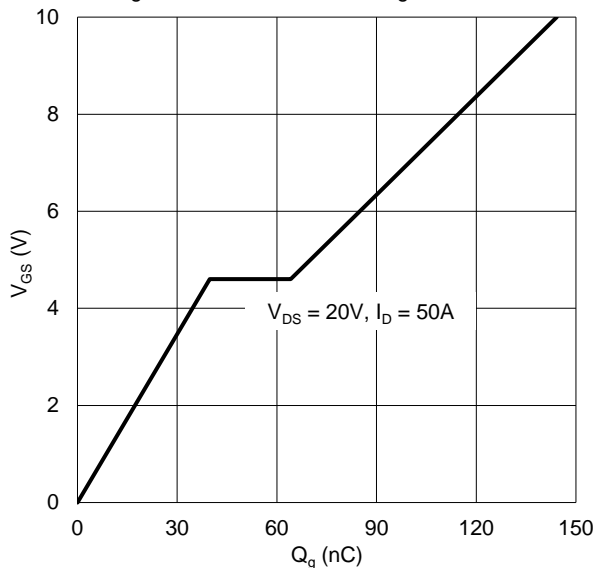


Figure 11. Gate Charge

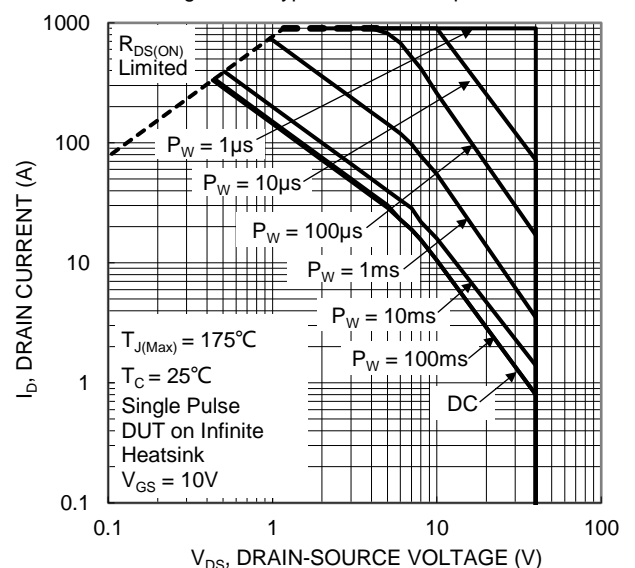


Figure 12. SOA, Safe Operation Area

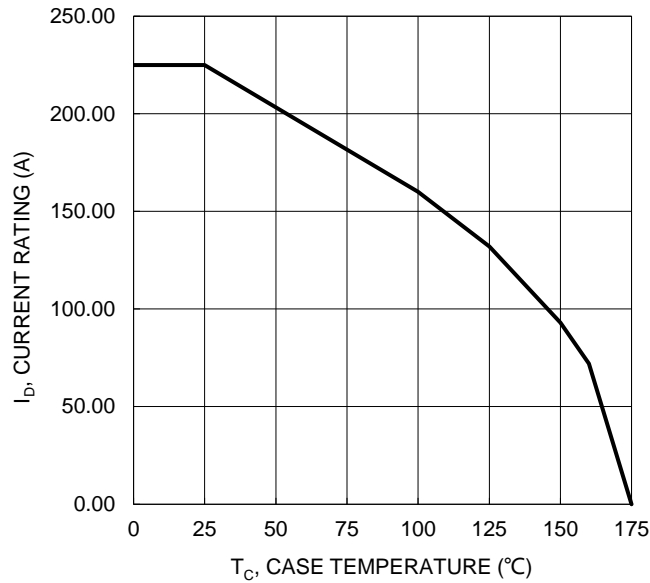


Figure 13. Current Derating

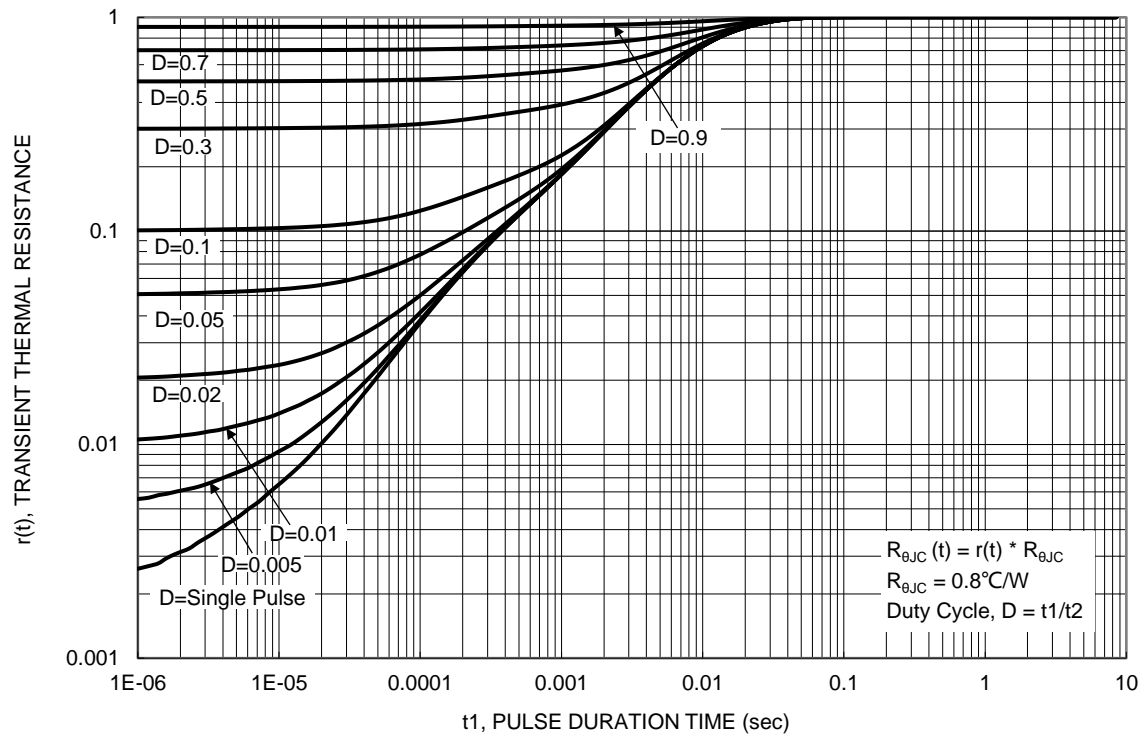
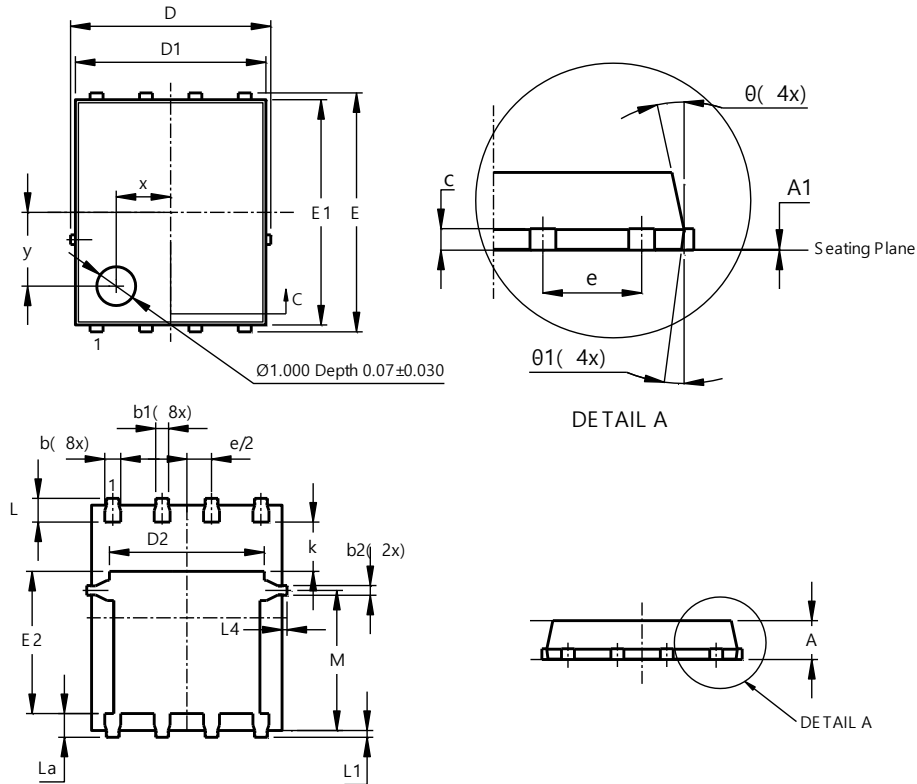


Figure 14. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8 (Type K)

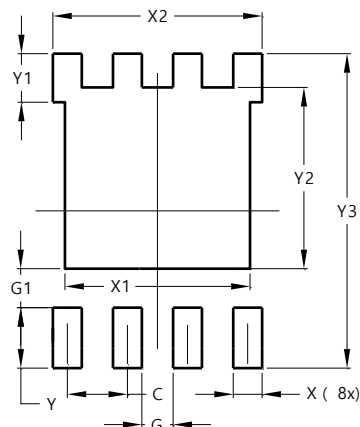


PowerDI5060-8 (Type K)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	0.02
b	0.33	0.51	0.41
b1	0.300	0.366	0.333
b2	0.20	0.35	0.25
c	0.23	0.33	0.277
D	5.15 BSC		
D1	4.85	4.95	4.90
D2	-	-	3.98
E	6.15 BSC		
E1	5.75	5.85	5.80
E2	3.56	3.725	3.66
e	1.27BSC		
k	-	-	1.27
L	0.51	0.71	0.61
La	0.51	0.675	0.61
L1	0.05	0.20	0.175
L4	-	-	0.125
M	3.50	3.71	3.605
x	-	-	1.400
y	-	-	1.900
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8 (Type K)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	3.910
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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